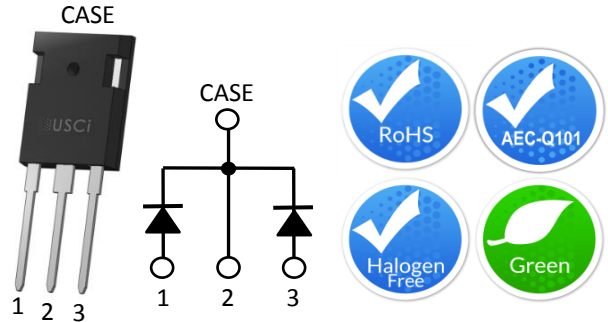


Description

United Silicon Carbide, Inc. offers the 3rd generation of high performance SiC Merged-PiN-Schottky (MPS) diodes. With zero reverse recovery charge and 175°C maximum junction temperature, these diodes are ideally suited for high frequency and high efficiency power systems with minimum cooling requirements.



Part Number	Package	Marking
UJ3D06520KSD	TO-247-3L	UJ3D06520KSD

Features

- ◆ 175°C maximum operating junction temperature
- ◆ Easy paralleling
- ◆ Extremely fast switching not dependent on temperature
- ◆ No reverse or forward recovery
- ◆ Enhanced surge current capability, MPS structure
- ◆ Excellent thermal performance, Ag sintered
- ◆ 100% UIS tested
- ◆ AEC-Q101 qualified

Typical Applications

- ◆ Power converters
- ◆ Industrial motor drives
- ◆ Switching-mode power supplies
- ◆ Power factor correction modules

Maximum Ratings

Parameter	Symbol	Test Conditions	Value (Leg/Device)	Units
DC blocking voltage	V_R		650	V
Repetitive peak reverse voltage, $T_j=25^\circ\text{C}$	V_{RRM}		650	V
Surge peak reverse voltage	V_{RSM}		650	V
Maximum DC forward current	I_F	$T_C = 152^\circ\text{C}$	10/20	A
Non-repetitive forward surge current sine halfwave	I_{FSM}	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$	70/140	A
		$T_C = 110^\circ\text{C}, t_p = 10\text{ms}$	60/120	
Repetitive forward surge current sine halfwave, $D=0.1$	I_{FRM}	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$	45.9/91.8	A
		$T_C = 110^\circ\text{C}, t_p = 10\text{ms}$	28.7/57.4	
Non-repetitive peak forward current	$I_{F,max}$	$T_C = 25^\circ\text{C}, t_p = 10\mu\text{s}$	455/910	A
		$T_C = 110^\circ\text{C}, t_p = 10\mu\text{s}$	455/910	
i^2t value	$\int i^2 dt$	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$	24.5/98	A^2s
		$T_C = 110^\circ\text{C}, t_p = 10\text{ms}$	18/72	
Power dissipation	P_{Tot}	$T_C = 25^\circ\text{C}$	136.4/272.8	W
		$T_C = 152^\circ\text{C}$	20.9/41.8	
Maximum junction temperature	$T_{J,max}$		175	$^\circ\text{C}$
Operating and storage temperature	T_J, T_{STG}		-55 to 175	$^\circ\text{C}$
Soldering temperatures, wavesoldering only allowed at leads	T_{sold}	1.6mm from case for 10s	260	$^\circ\text{C}$

Electrical Characteristics

T_J = +25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Value (Leg/Device)			Units
			Min	Typ	Max	
Forward voltage	V _F	I _F = 10/20A, T _J = 25°C	-	1.5	1.7	V
		I _F = 10/20A, T _J =150°C	-	1.68	2	
		I _F = 10/20A, T _J =175°C	-	1.75	2.1	
Reverse current	I _R	V _R =650V, T _J =25°C	-	10/20	60/120	μA
		V _R =650V, T _J =175°C	-	150/300		
Total capacitive charge ⁽¹⁾	Q _C	V _R =400V		23/46		nC
Total capacitance	C	V _R =1V, f=1MHz		327/654		pF
		V _R =300V, f=1MHz		38/76		
		V _R =600V, f=1MHz		34/68		
Capacitance stored energy	E _C	V _R =400V		3.4/6.8		μJ

(1) Q_C is independent on T_J, di_F/dt, and I_F as shown in the application note USCi_AN0011.

Thermal characteristics

Parameter	symbol	Test Conditions	Value (Leg/Device)			Units
			Min	Typ	Max	
Thermal resistance	R _{θJC}			0.82/0.41	1.1/0.55	°C/W

Typical Performance

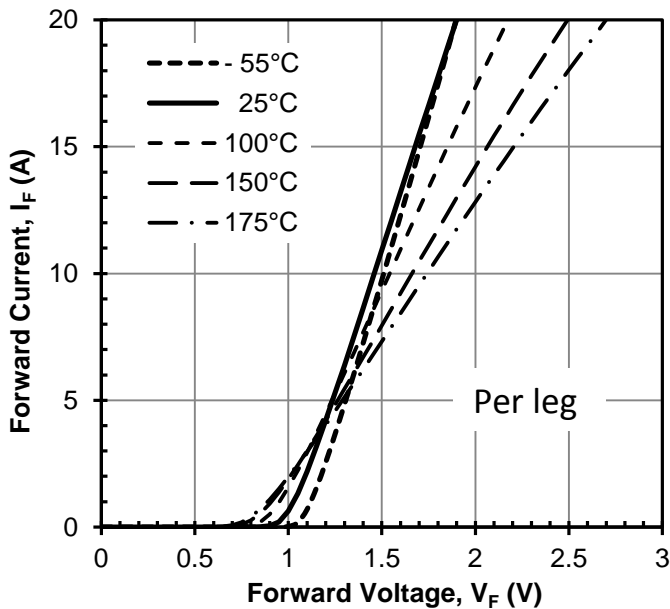


Figure 1 Typical forward characteristics per leg

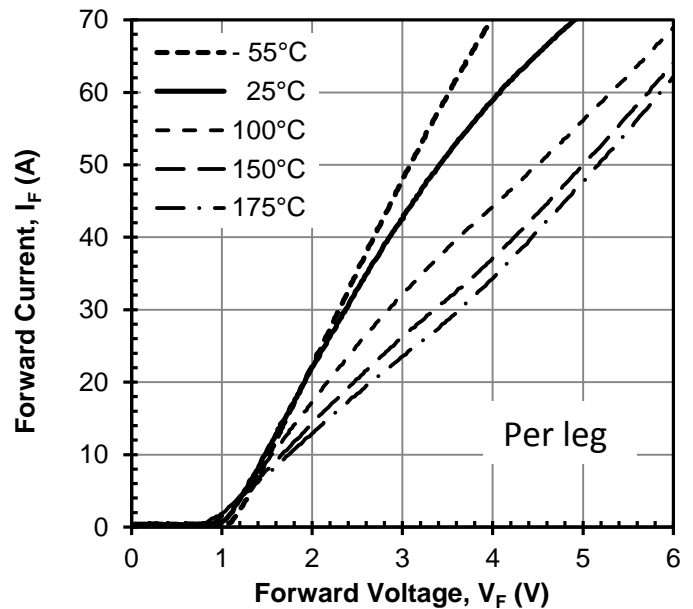


Figure 2 Typical forward characteristics in surge current per leg

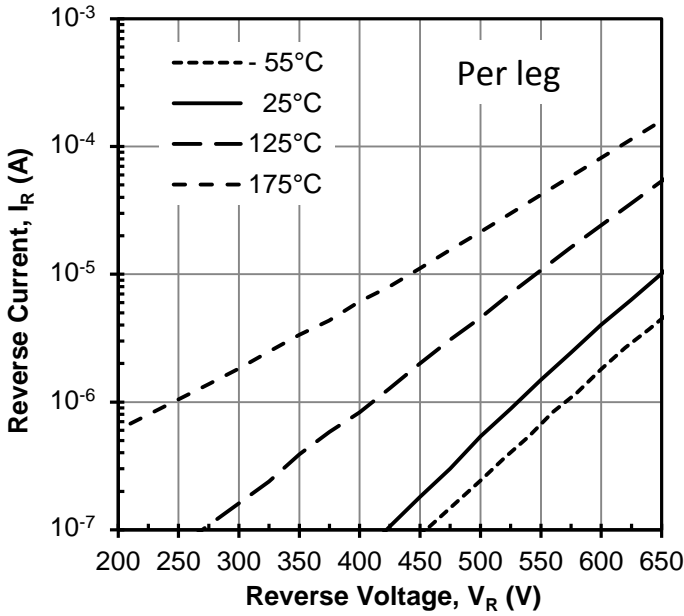


Figure 3 Typical reverse characteristics per leg

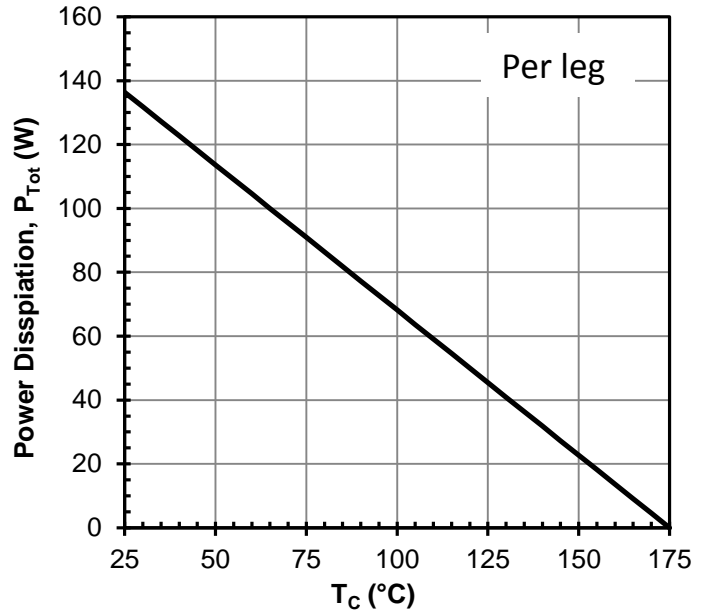


Figure 4 Power dissipation per leg

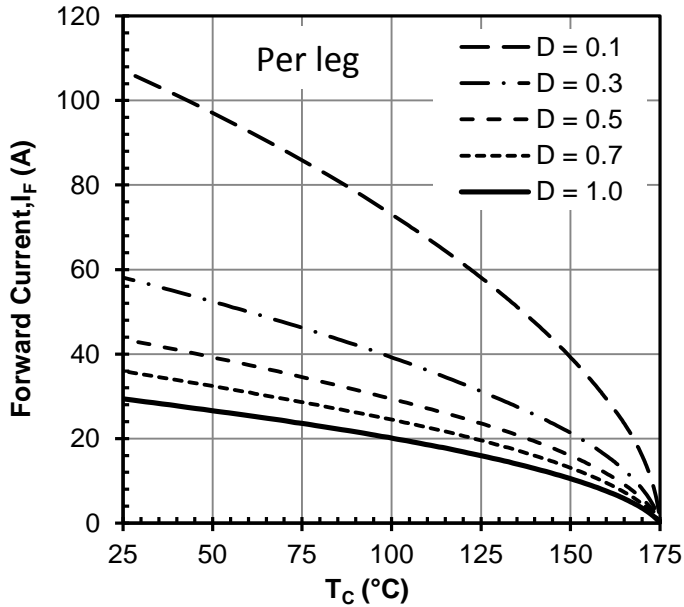


Figure 5 Diode forward current per leg

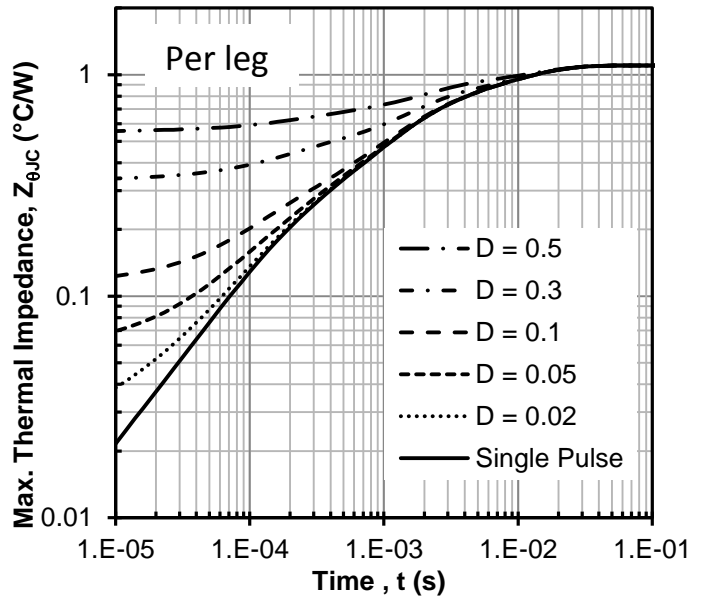


Figure 6 Maximum transient thermal impedance per leg

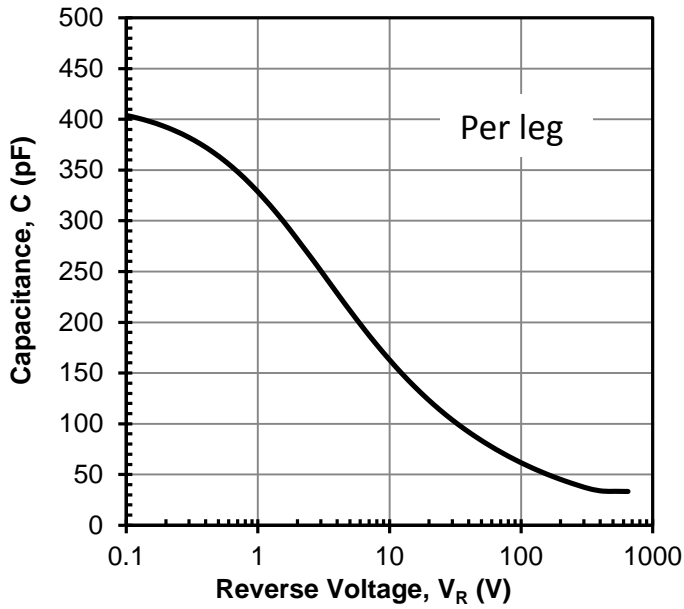


Figure 7 Capacitance per leg vs. reverse voltage at 1MHz

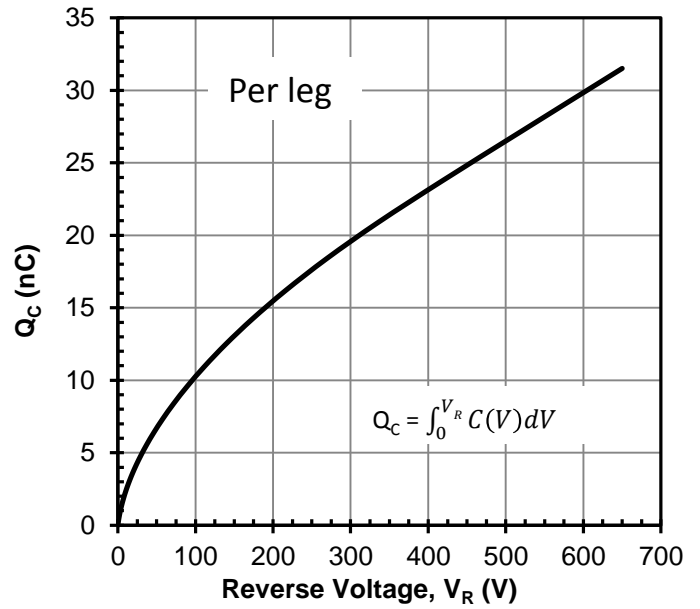


Figure 8 Typical capacitive charge per leg vs. reverse voltage

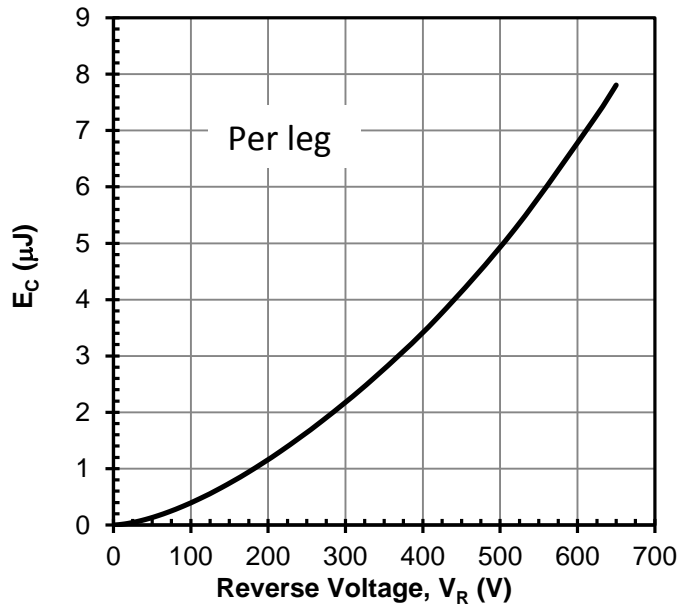


Figure 9 Typical capacitance stored energy per leg vs. reverse voltage

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